

## ABSTRACT

A wafer provided with a resist pattern is placed in a dry etching apparatus, and an antireflection film and a silicon nitride film are dry-etched using the resist pattern as a mask. Thus, a first deposit deposited on a side face of the resist pattern facing inwardly with respect to the center of the wafer, and a second deposit deposited on a side face of the resist pattern facing outwardly are both relatively thickly adhered. An etching gas used in this case is a gas mixture containing  $\text{SF}_6$ ,  $\text{CHF}_3$  and Ar.